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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE (REV. 05/03) 	ATTY. DOCKET NO. BU-021AX	APPLICATION NO. 10/790,403
	APPLICANT: M. Selim Unlu et al.	
	FILING DATE March 1, 2004	TC ART UNIT

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION/ ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE
MW	US 5,770,511	06/23/1998	Matsumoto et al	438	406	
MW	US 5,376,215	12/27/1994	Ohta et al	156	345	
MW	US 4,670,765	06/02/1987	Nakamura et al	357	30	
MW	US 5,757,986	05/26/1998	Crampton et al	385	2	
MW	US 5,767,507	06/16/1998	Unlu et al	250	225	
MW	US 5,710,057	01/20/1998	Kenney	437	62	
MW	US 5,671,914	09/30/1997	Kalkhoran et al	257	77	

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## OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)

MW	Ishikawa et al., "Epitaxy-ready Si/SiO <sub>2</sub> Bragg Reflectors by Multiple Separation-by-Implanted Oxygen", Appl. Phys. Letters, Vol 69, No. 25 16 December 1996.
MW	Sinnis et al. "Silicon-based Resonant-cavity-enhanced Photodiode with a Buried SiO <sub>2</sub> Reflector", Appl. Phys. Letters, Vol 74, No. 9, 1 March 1999.
MW	Schow et al., "Design and Implementation of High-speed Planar Si Photodiodes Fabricated on SOI Substrates", IEEE Journal of Quantum Electronics, Vol. 35, No. 10, October 1999.
MW	Schaub et al., "Resonant-cavity-enhanced High-speed Si Photodiode Grown by Epitaxial Lateral Overgrowth", IEEE Photonics Technology Letters, Vol. 11, No. 12, 12 December 1999.
MW	Jalali et al., "Advances in Silicon-on-Insulator Optoelectronics", IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 6, Nov/Dec 1998.
MW	Fukatsu et al., "Spectral Modulation of Luminescence of Strained Si <sub>1-x</sub> Ge <sub>x</sub> /Si Quantum Wells in a Vertical Cavity with air/Si and Si/SiO <sub>2</sub> Interface Mirrors", Appl. Phys. Letters, Vol. 65, No. 24, 12 December 1994.

EXAMINER MW/iczewski	DATE CONSIDERED 02/2006
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\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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<i>mw</i>	US 5,498,863	03/12/1996	Miller	250	214.1	
<i>mw</i>	US 5,389,797	02/14/1995	Bryan et al	257	21	
<i>mw</i>	US 5,455,421	10/03/1995	Spears	250	338.4	
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<i>mw</i>	Yonehara et al., "Epitaxial Layer Transfer by Bond and Etch Back of Porous Si", Appl Phys. Letters, Vol. 64, No. 16, 18 April 1994.
<i>mw</i>	Tan et al., "Modeling and Performance of Wafer-Fused Resonant-Cavity Enhanced Photodetectors", IEEE Journal of Quantum Electronics, Vol. 31, No. 10, 10 October 1995.
<i>mw</i>	Bean et al., "High-Speed Polysilicon Resonant-Cavity Photodiode with SiO <sub>2</sub> -Si Bragg Reflectors", IEEE Photonics Technology Letters, Col. 9, No. 6, June 1997.
<i>mw</i>	Diaz et al., "Si/SiO <sub>2</sub> Resonant Cavity Photodetector", Appl. Phys. Letters, Vol. 69, No. 19, 4 November 1996.
<i>mw</i>	Murtaza et al., "Short-Wavelength, High-Speed, Si-Based Resonant-Cavity Photodetector", IEEE Photonics Technology Letters, Vol. 8, No. 7, July 1996.
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*02/2006*

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MW	Wada et al., "A New Approach of Photonic Bandgap Formation-Wafer Bonding and Delamination Technique", Extended Abstracts of the 1998 International Conference on Solid State Devices and Materials, pp 382-383 1998.
MW	Unlu et al., "Resonant Cavity Enhanced Photonic Devices", Journal Appl. Phys. Vol. 78, No. 2, 15 July 1995.

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